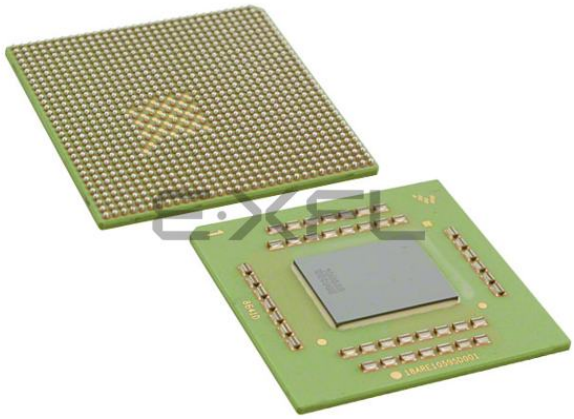

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.25GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641tvu1250hc

  - Support for PCI-Express message-shared interrupts (MSIs)
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects support eight external slaves
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and the remote masters
  - Supports transfers to or from any local memory or I/O port
  - Ability to start and flow control each DMA channel from external 3-pin interface
- Device performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- IEEE 1149.1-compatible, JTAG boundary scan
- Available as 1023 pin Hi-CTE flip chip ceramic ball grid array (FC-CBGA)

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Absolute Maximum Value	Unit	Notes
Input voltage	DDR and DDR2 SDRAM signals	D*n*_MV_{IN}	– 0.3 to (D*n*_GV_{DD} + 0.3)	V	5
	DDR and DDR2 SDRAM reference	D*n*_MV_{REF}	– 0.3 to (D*n*_GV_{DD}/2 + 0.3)	V	—
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to (LV_{DD}+ 0.3) GND to (TV_{DD}+ 0.3)	V	5
	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{IN}	GND to (OV_{DD}+ 0.3)	V	5
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. Core 1 characteristics apply only to MPC8641D. If two separate power supplies are used for V_{DD}_Core0 and V_{DD}_Core1, they must be kept within 100 mV of each other during normal run time.
3. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
4. The 3.63V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75V maximum applies. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
5. During run time (M,L,T,O)V_{IN} and D*n*_MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for the MPC8641. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed. For details on order information and specific operating conditions for parts, see Section 21, "Ordering Information."

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Cores supply voltages	V_{DD}_Core0, V_{DD}_Core1	1.10 ± 50 mV	V	1, 2, 8
		1.05 ± 50 mV		1, 2, 7
		0.95 ± 50 mV		1, 2, 12
Cores PLL supply	AV_{DD}_Core0, AV_{DD}_Core1	1.10 ± 50 mV	V	8, 13
		1.05 ± 50 mV		7, 13
		0.95 ± 50 mV		12, 13
SerDes Transceiver Supply (Ports 1 and 2)	SV_{DD}	1.10 ± 50 mV	V	8, 11
		1.05 ± 50 mV		7, 11

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8641. Note that DDR SDRAM is D*n*_GV_{DD}(typ) = 2.5 V and DDR2 SDRAM is D*n*_GV_{DD}(typ) = 1.8 V.

6.1 DDR SDRAM DC Electrical Characteristics

Table 13 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8641 when D*n*_GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM DC Electrical Characteristics for D*n*_GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	D*n*_GV_{DD}	1.71	1.89	V	1
I/O reference voltage	D*n*_MV_{REF}	0.49 × D*n*_GV_{DD}	0.51 × D*n*_GV_{DD}	V	2
I/O termination voltage	V_{TT}	D*n*_MV_{REF} – 0.04	D*n*_MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	D*n*_MV_{REF}+ 0.125	D*n*_GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	D*n*_MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. D*n*_GV_{DD} is expected to be within 50 mV of the DRAM D*n*_GV_{DD} at all times.
2. D*n*_MV_{REF} is expected to be equal to 0.5 × D*n*_GV_{DD}, and to track D*n*_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on D*n*_MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to D*n*_MV_{REF}. This rail should track variations in the DC level of D*n*_MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ D*n*_GV_{DD}.

Table 14 provides the DDR2 capacitance when D*n*_GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for D*n*_GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{\text{DQS}}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{\text{DQS}}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. D*n*_GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = D*n*_GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 24. GMII, MII, RMII, TBI and FIFO DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	3

Notes:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4.
3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Table 25. GMII, RGMII, RTBI, TBI and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.375	2.625	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	—	0.40	V	—
Input high voltage	V_{IH}	1.70	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	μA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	μA	3

Note:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4.
3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI and RTBI are specified in "Section 8, "Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management."

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 38.

Table 38. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.135	3.465	V
Output high voltage (OV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	—	V
Output low voltage (OV_{DD} =Min, I_{OL} = 1.0 mA)	V_{OL}	—	0.50	V
Input high voltage	V_{IH}	1.70	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current (OV_{DD} = Max, V_{IN} [1] = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 MII Management AC Electrical Specifications

Table 39 provides the MII management AC timing specifications.

Table 39. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	2.5	—	9.3	MHz	2, 4
MDC period	t_{MDC}	80	—	400	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$16*t_{MPXCLK}$	—	—	ns	5
MDC to MDIO delay	t_{MDKHDX}	10	—	$16*t_{MPXCLK}$	ns	3, 5
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—

Table 39. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4
MDC fall time	t_{MDHF}	—	—	10	ns	4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed. (The maximum frequency is the maximum platform frequency divided by 64.)
3. This parameter is dependent on the system clock speed. (That is, for a system clock of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a system clock of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz.)
4. Guaranteed by design.
5. t_{MPXCLK} is the platform (MPX) clock

Figure 23 provides the AC test load for eTSEC.

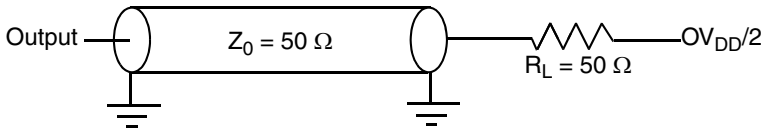

Figure 23. eTSEC AC Test Load

NOTE

Output will see a 50-Ω load since what it sees is the transmission line.

Figure 24 shows the MII management AC timing diagram.

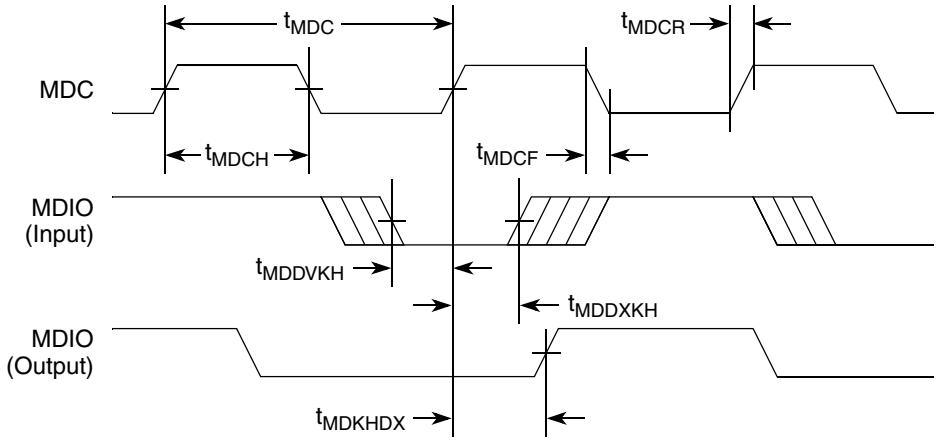

Figure 24. MII Management Interface Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8641.

10.1 Local Bus DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the local bus interface operating at OV_{DD} = 3.3 V DC.

Table 40. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = OV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

Table 41 describes the timing parameters of the local bus interface at OV_{DD} = 3.3 V with PLL enabled. For information about the frequency range of local bus see Section 18.1, "Clock Ranges."

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Local Bus Duty Cycle	t_{LBKH}/t_{LBK}	45	55	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	—
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	—

- The input amplitude requirement
  - This requirement is described in detail in the following sections.

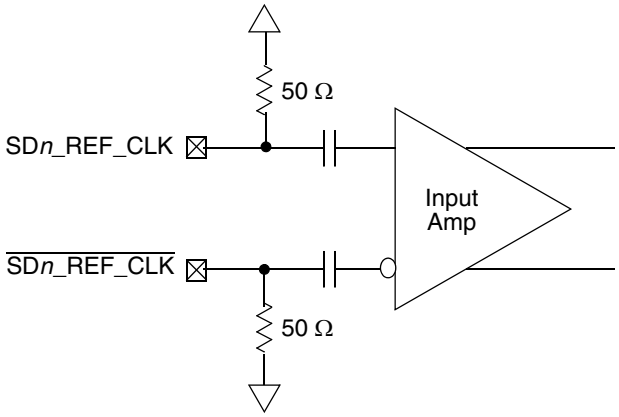

Figure 39. Receiver of SerDes Reference Clocks

13.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the MPC8641D SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- **Differential Mode**
  - The input amplitude of the differential clock must be between 400 mV and 1600 mV differential peak-peak (or between 200 mV and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800mV and greater than 200 mV. This requirement is the same for both external DC-coupled or AC-coupled connection.
  - For **external DC-coupled** connection, as described in Section 13.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 mV and 400 mV. Figure 40 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
  - For **external AC-coupled** connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SGND. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SGND). Figure 41 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- **Single-ended Mode**
  - The reference clock can also be single-ended. The SD*n*_REF_CLK input amplitude (single-ended swing) must be between 400 mV and 800 mV peak-peak (from Vmin to Vmax) with $\overline{\text{SD}n\text{\_REF\_CLK}}$ either left unconnected or tied to ground.

13.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

Table 47 describes some AC parameters common to PCI Express and Serial RapidIO protocols.

Table 47. SerDes Reference Clock Common AC Parameters

At recommended operating conditions with XV_{DD}_SRDS1 or XV_{DD}_SRDS2 = 1.1V ± 5% and 1.05V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V_{IH}	+200		mV	2
Differential Input Low Voltage	V_{IL}	—	–200	mV	2
Rising edge rate (SD*n*_REF_CLK) to falling edge rate ($\overline{\text{SD}n\text{\_REF\_CLK}}$) matching	Rise-Fall Matching	—	20	%	1, 4

Notes:

1. Measurement taken from single ended waveform.
2. Measurement taken from differential waveform.
3. Measured from –200 mV to +200 mV on the differential waveform (derived from SD*n*_REF_CLK minus $\overline{\text{SD}n\text{\_REF\_CLK}}$). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 47.
4. Matching applies to rising edge rate for SD*n*_REF_CLK and falling edge rate for $\overline{\text{SD}n\text{\_REF\_CLK}}$. It is measured using a 200 mV window centered on the median cross point where SDn_REF_CLK rising meets $\overline{\text{SD}n\text{\_REF\_CLK}}$ falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The Rise Edge Rate of SD*n*_REF_CLK should be compared to the Fall Edge Rate of $\overline{\text{SD}n\text{\_REF\_CLK}}$, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 48.

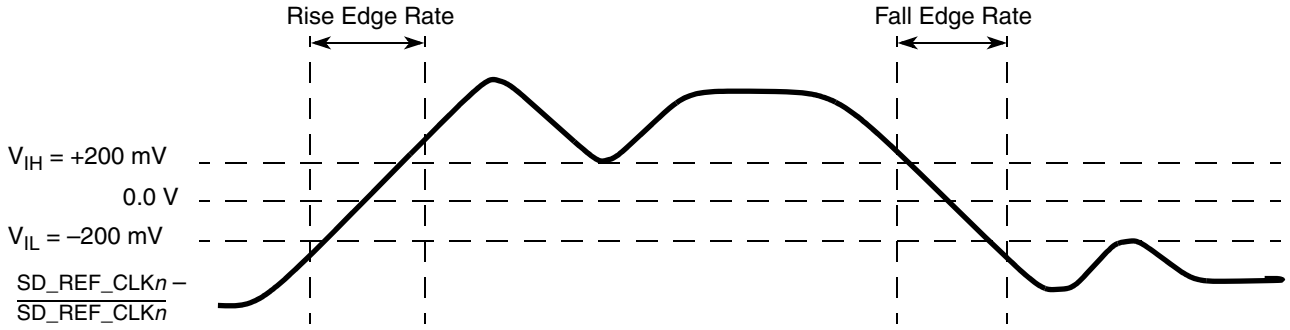

Figure 47. Differential Measurement Points for Rise and Fall Time

Table 57. Long Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	–0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/– 100 ppm

For each baud rate at which an LP-Serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the Transmitter Output Compliance Mask shown in Figure 54 with the parameters specified in Table 58 when measured at the output pins of the device and the device is driving a 100 Ω +/–5% differential resistive load. The output eye pattern of an LP-Serial transmitter that implements pre-emphasis (to equalize the link and reduce inter-symbol interference) need only comply with the Transmitter Output Compliance Mask when pre-emphasis is disabled or minimized.

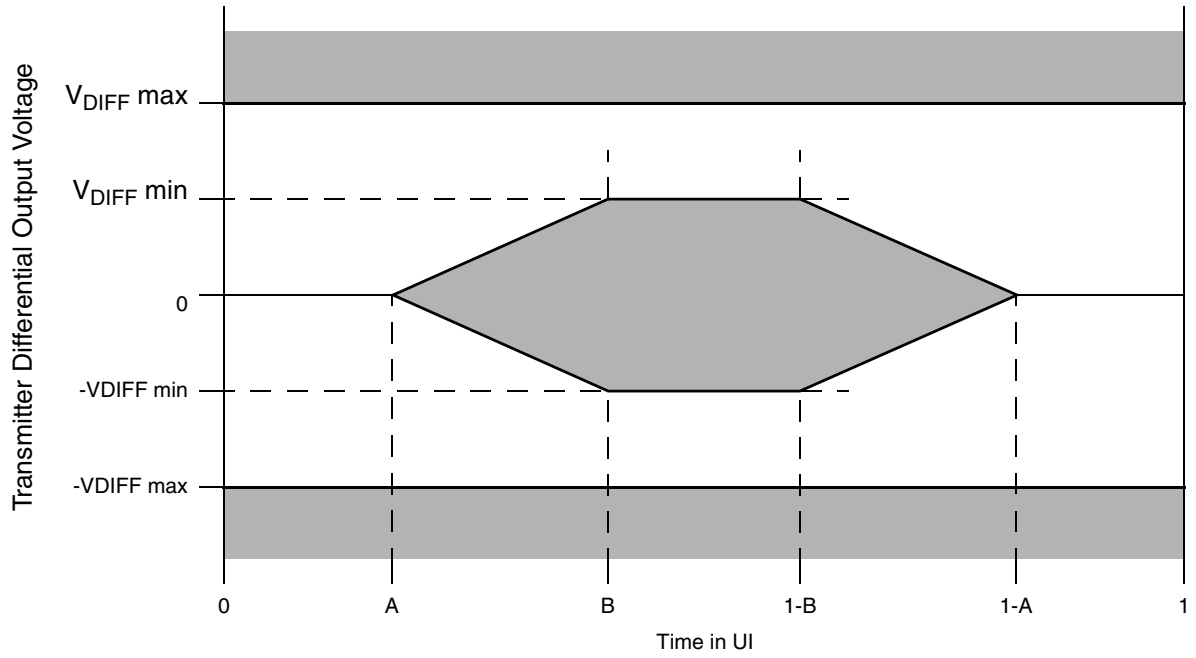

Figure 54. Transmitter Output Compliance Mask

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
SD1_PLL_TPA	T28	Analog	SV_{DD}	13, 18
SD1_DLL_TPD	N28	O	SV_{DD}	13, 17
SD1_DLL_TPA	P31	Analog	SV_{DD}	13, 18
High Speed I/O Interface 2 (SERDES 2)[4]				
SD2_TX[0:3]	Y24, AA27, AB25, AC27	O	SV_{DD}	—
SD2_TX[4:7]	AE27, AG27, AJ27, AL27	O	SV_{DD}	34
$\overline{\text{SD2\_TX}}$[0:3]	Y25, AA28, AB26, AC28	O	SV_{DD}	—
$\overline{\text{SD2\_TX}}$[4:7]	AE28, AG28, AJ28, AL28	O	SV_{DD}	34
SD2_RX[0:3]	Y30, AA32, AB30, AC32	I	SV_{DD}	32
SD2_RX[4:7]	AH30, AJ32, AK30, AL32	I	SV_{DD}	32, 35
$\overline{\text{SD2\_RX}}$[0:3]	Y29, AA31, AB29, AC31	I	SV_{DD}	—
$\overline{\text{SD2\_RX}}$[4:7]	AH29, AJ31, AK29, AL31	I	SV_{DD}	35
SD2_REF_CLK	AE32	I	SV_{DD}	—
$\overline{\text{SD2\_REF\_CLK}}$	AE31	I	SV_{DD}	—
SD2_IMP_CAL_TX	AM29	Analog	SV_{DD}	19
SD2_IMP_CAL_RX	AA26	Analog	SV_{DD}	30
SD2_PLL_TPD	AF29	O	SV_{DD}	13, 17
SD2_PLL_TPA	AF31	Analog	SV_{DD}	13, 18
SD2_DLL_TPD	AD29	O	SV_{DD}	13, 17
SD2_DLL_TPA	AD30	Analog	SV_{DD}	13, 18
Special Connection Requirement pins				
No Connects	K24, K25, P28, P29, W26, W27, AD25, AD26	—	—	13
Reserved	H30, R32, V28, AG32	—	—	14
Reserved	H29, R31, W28, AG31	—	—	15
Reserved	AD24, AG26	—	—	16
Ethernet Miscellaneous Signals[5]				
EC1_GTX_CLK125	AL23	I	LV_{DD}	39
EC2_GTX_CLK125	AM23	I	TV_{DD}	39
EC_MDC	G31	O	OV_{DD}	—
EC_MDIO	G32	I/O	OV_{DD}	—
eTSEC Port 1 Signals[5]				

Table 65. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	1000, 1250, 1333, 1500MHz			
	Min	Max		
Memory bus clock frequency	200	300	MHz	1, 2

Notes:
1. **Caution:** The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 18.2, "MPX to SYSCLK PLL Ratio," and Section 18.3, "e600 to MPX clock PLL Ratio," for ratio settings.
2. The memory bus clock speed is half the DDR/DDR2 data rate, hence, half the MPX clock frequency.

Table 66. Platform/MPX bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	1000, 1250, 1333, 1500MHz			
	Min	Max		
Platform/MPX bus clock frequency	400	500-600	MHz	1, 2

Notes:
1. **Caution:** The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 18.2, "MPX to SYSCLK PLL Ratio," and Section 18.3, "e600 to MPX clock PLL Ratio," for ratio settings.
2. Platform/MPX frequencies between 400 and 500 MHz are not supported.

Table 67. Local Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	1000, 1250, 1333, 1500MHz			
	Min	Max		
Local bus clock speed (for Local Bus Controller)	25	133	MHz	1

Notes:
1. The Local bus clock speed on LCLK[0:2] is determined by MPX clock divided by the Local Bus PLL ratio programmed in LCRR[CLKDIV]. See the reference manual for the MPC8641D for more information on this.

18.2 MPX to SYSCLK PLL Ratio

The MPX clock is the clock that drives the MPX bus, and is also called the platform clock. The frequency of the MPX is set using the following reset signals, as shown in Table 68:

- SYSCLK input signal

18.4.1 SYSCLK to Platform Frequency Options

Table 70 shows some SYSCLK frequencies and the expected MPX frequency values based on the MPX clock to SYSCLK ratio. Note that frequencies between 400 MHz and 500 MHz are NOT supported on the platform. See note regarding *cfg_platform_freq* in Section 17, "Signal Listings," because it is a reset configuration pin that is related to platform frequency.

Table 70. Frequency Options of SYSCLK with Respect to Platform/MPX Clock Speed

MPX to SYSCLK Ratio	SYSCLK (MHz)					
	66	83	100	111	133	167
	Platform/MPX Frequency (MHz)[1]					
2						
3					400	500
4			400		533	
5			500	555		
6	400	500	600			
8	533					
9	600					

1 SYSCLK frequency range is 66-167 MHz. Platform clock/ MPX frequency range is 400 MHz, 500-600 MHz.

18.4.2 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency <= platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 127 MHz

For FIFO encoded mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

The Bergquist Company 18930 West 78th St. Chanhassen, MN 55317 Internet: www.bergquistcompany.com	800-347-4572
Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01801 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Corporate Center PO Box 994 Midland, MI 48686-0994 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674
Thermagon Inc. 4707 Detroit Ave. Cleveland, OH 44102 Internet: www.thermagon.com	888-246-9050

The following section provides a heat sink selection example using one of the commercially available heat sinks.

19.2.3 Heat Sink Selection Example

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_j = T_i + T_r + (R_{\theta JC} + R_{\theta int} + R_{\theta sa}) \times P_d$$

where:

T_j is the die-junction temperature
T_i is the inlet cabinet ambient temperature
T_r is the air temperature rise within the computer cabinet
$R_{\theta JC}$ is the junction-to-case thermal resistance
$R_{\theta int}$ is the adhesive or interface material thermal resistance
$R_{\theta sa}$ is the heat sink base-to-ambient thermal resistance
P_d is the power dissipated by the device

During operation, the die-junction temperatures (T_j) should be maintained less than the value specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_i) may range from 30° to 40°C. The air temperature rise within a cabinet (T_r) may be in the range of 5° to 10°C. The thermal resistance of the thermal interface material ($R_{\theta int}$) is typically about 0.2°C/W. For

example, assuming a T_i of 30°C, a T_r of 5°C, a package $R_{\theta JC}$ = 0.1, and a typical power consumption (P_d) of 43.4 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 0.2°C/W + \theta_{sa}) \times 43.4\ W$

For this example, a $R_{\theta sa}$ value of 1.32 °C/W or less is required to maintain the die junction temperature below the maximum value of Table 2.

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, and so on.

Due to the complexity and variety of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board as well as system-level designs.

For system thermal modeling, the MPC8641 thermal model is shown in Figure 62. Four cuboids are used to represent this device. The die is modeled as 12.4x15.3 mm at a thickness of 0.86 mm. See Section 3, "Power Characteristics" for power dissipation details. The substrate is modeled as a single block 33x33x1.2 mm with orthotropic conductivity: 13.5 W/(m • K) in the xy-plane and 5.3 W/(m • K) in the z-direction. The die is centered on the substrate. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate with a conductivity of 5.3 W/(m • K) in the thickness dimension of 0.07 mm. Because the bump/underfill is modeled with zero physical dimension (collapsed height), the die thickness was slightly enlarged to provide the correct height. The C5 solder layer is modeled as a cuboid with dimensions 33x33x0.4 mm and orthotropic thermal conductivity of 0.034 W/(m • K) in the xy-plane and 9.6 W/(m • K) in the z-direction. An LGA solder layer would be modeled as a collapsed thermal resistance with thermal conductivity of 9.6W/(m • K) and an effective height of 0.1 mm. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

Another useful equation is:

$$V_H - V_L = n\frac{KT}{q}\left[ln\frac{I_H}{I_L}\right]$$

Where:

I_{fw} = Forward current
I_s = Saturation current
V_d = Voltage at diode
V_f = Voltage forward biased
V_H = Diode voltage while I_H is flowing
V_L = Diode voltage while I_L is flowing
I_H = Larger diode bias current
I_L = Smaller diode bias current
q = Charge of electron (1.6×10^{-19} C)
n = Ideality factor (normally 1.0)
K = Boltzman's constant (1.38×10^{-23} Joules/K)
T = Temperature (Kelvins)

The ratio of I_H to I_L is usually selected to be 10:1. The above simplifies to the following:

$$V_H - V_L = 1.986 \times 10^{-4} \times nT$$

Solving for T, the equation becomes:

$$nT = \frac{V_H - V_L}{1.986 \times 10^{-4}}$$

20 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8641.

20.1 System Clocking

This device includes six PLLs, as follows:

1. The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 18.2, "MPX to SYSCLK PLL Ratio."
2. The dual e600 Core PLLs generate the e600 clock from the externally supplied input.
3. The local bus PLL generates the clock for the local bus.
4. There are two internal PLLs for the SerDes block.

20.2 Power Supply Design and Sequencing

20.2.1 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits per PLL power supply as illustrated in Figure 64, one to each of the AV_{DD} type pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} type pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} type pin, which is on the periphery of the footprint, without the inductance of vias.

Figure 63 and Figure 64 show the PLL power supply filter circuits for the platform and cores, respectively.

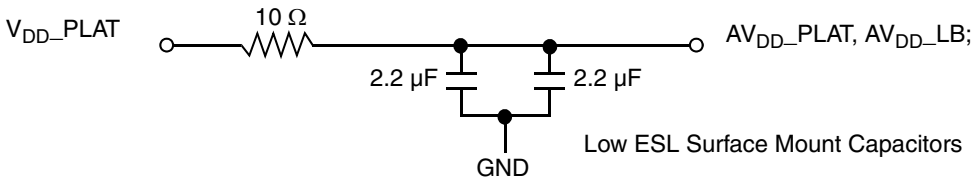

Figure 63. MPC8641 PLL Power Supply Filter Circuit (for platform and Local Bus)

For other pin pull-up or pull-down recommendations of signals, please see Section 17, "Signal Listings."

20.7 Output Buffer DC Impedance

The MPC8641 drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 66). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

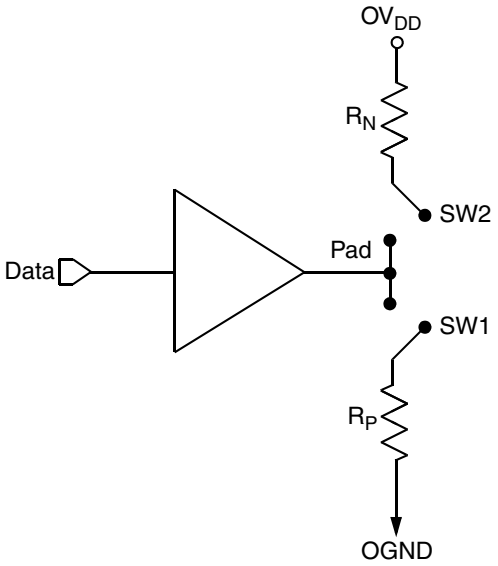

Figure 66. Driver Impedance Measurement

Table 73 summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 73. Impedance Characteristics

Impedance	DUART, Control, Configuration, Power Management	PCI Express	DDR DRAM	Symbol	Unit
R_N	43 Target	25 Target	20 Target	Z_0	W
R_P	43 Target	25 Target	20 Target	Z_0	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

20.8 Configuration Pin Muxing

The MPC8641 provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform /system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio and e600 PLL ratio configuration pins are not equipped with these default pull-up devices.

20.9 JTAG Configuration Signals

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 68. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{\text{TRST}}$ signal is optional in the IEEE 1149.1 specification, but is provided on all processors that implement the Power Architecture technology. The device requires $\overline{\text{TRST}}$ to be asserted during reset conditions to ensure the JTAG boundary logic does not interfere with normal chip operation. While it is possible to force the TAP controller to the reset state using only the TCK and TMS signals, more reliable power-on reset performance will be obtained if the $\overline{\text{TRST}}$ signal is asserted during power-on reset. Because the JTAG interface is also used for accessing the common on-chip processor (COP) function, simply tying $\overline{\text{TRST}}$ to $\overline{\text{HRESET}}$ is not practical.

The COP function of these processors allows a remote computer system (typically a PC with dedicated hardware and debugging software) to access and control the internal operations of the processor. The COP port connects primarily through the JTAG interface of the processor, with some additional status monitoring signals. The COP port requires the ability to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$ in order to fully control the processor. If the target system has independent reset sources, such as voltage monitors, watchdog timers, power supply failures, or push-button switches, then the COP reset signals must be merged into these signals with logic.

The arrangement shown in Figure 67 allows the COP port to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$, while ensuring that the target can drive $\overline{\text{HRESET}}$ as well.

21 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 21.1, "Part Numbers Fully Addressed by This Document."

21.1 Part Numbers Fully Addressed by This Document

Table 74 provides the Freescale part numbering nomenclature for the MPC8641. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number.

Table 74. Part Numbering Nomenclature

MC	nnnn	x	xx	nnnn	x	x
Product Code	**Part Identifier**	**Core Count**	**Package [1]**	**Core Processor Frequency [2] (MHz)**	**DDR speed (MHz)**	**Product Revision Level**
MC	8641	Blank = Single Core D = Dual Core	HX = High-lead HCTE FC-CBGA VU = RoHS lead-free HCTE FC-CBGA[5] VJ = lead-free HCTE FC-CBGA[6]	1000, 1250, 1333, 1500	N = 500 MHz[4] K = 600 MHz J = 533 MHz H = 500 MHz G = 400 MHz	Revision B = 2.0 System Version Register Value for Rev B: 0x8090_0020 - MPC8641 0x8090_0120 - MPC8641D Revision C = 2.1 System Version Register Value for Rev C: 0x8090_0021 - MPC8641 0x8090_0121 - MPC8641D Revision E = 3.0 System Version Register Value for Rev E: 0x8090_0030 - MPC8641 0x8090_0130 - MPC8641D

Notes:

1. See Section 16, "Package," for more information on available package types.
2. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.
3. The P prefix in a Freescale part number designates a "Pilot Production Prototype" as defined by Freescale SOP 3-13. These parts have only preliminary reliability and characterization data. Before pilot production prototypes may be shipped, written authorization from the customer must be on file in the applicable sales office acknowledging the qualification status and the fact that product changes may still occur while shipping pilot production prototypes.
4. Part Number MC8641xxx1000NX is our low V_{DD}_Core*n* device. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V.
5. VU part number is RoHS compliant with the permitted exception of the C4 die bumps.
6. VJ part number is entirely lead-free including the C4 die bumps.